

MOS FIELD EFFECT TRANSISTOR 2SK2414, 2414-Z

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK2414 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-Resistance
 $R_{DS(on)1} = 70 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 5.0 \text{ A)}$
 $R_{DS(on)2} = 95 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4 \text{ V, } I_D = 5.0 \text{ A)}$
- Low C_{iss} : $C_{iss} = 860 \text{ pF TYP.}$
- Built-in G-S Gate Protection Diodes
- High Avalanche Capability Ratings

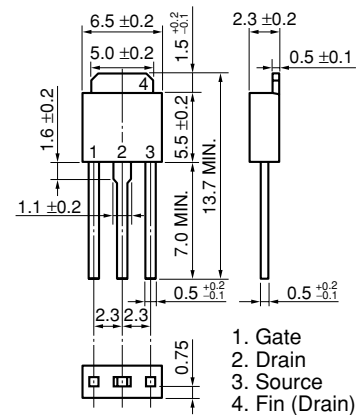
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ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ }^\circ\text{C}$)

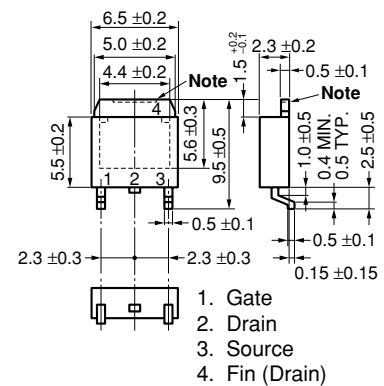
Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 10	A
Drain Current (pulse) Note 1	$I_{D(pulse)}$	± 40	A
Total Power Dissipation ($T_C = 25 \text{ }^\circ\text{C}$)	P_{T1}	20	W
Total Power Dissipation ($T_A = 25 \text{ }^\circ\text{C}$)	P_{T2}	1.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$
Single Avalanche Current Note 2	I_{AS}	10	A
Single Avalanche Energy Note 2	E_{AS}	10	mJ

- Notes 1** $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1 \%$
2 Starting $T_{ch} = 25 \text{ }^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

<R> PACKAGE DIMENSIONS (Unit: mm)



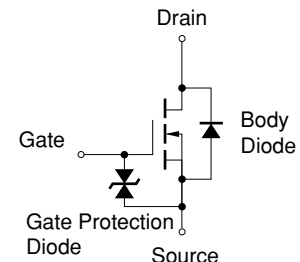
MP-3



Note The depth of notch at the top of the fin is from 0 to 0.2 mm.

MP-3Z (SURFACE MOUNT TYPE)

EQUIVALENT CIRCUIT

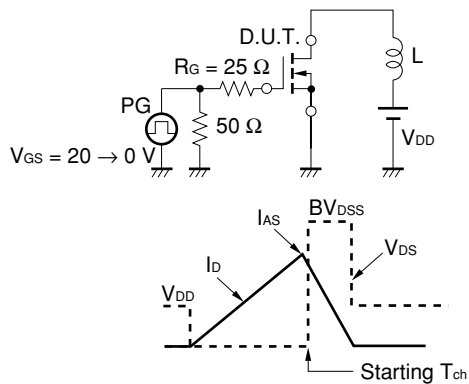


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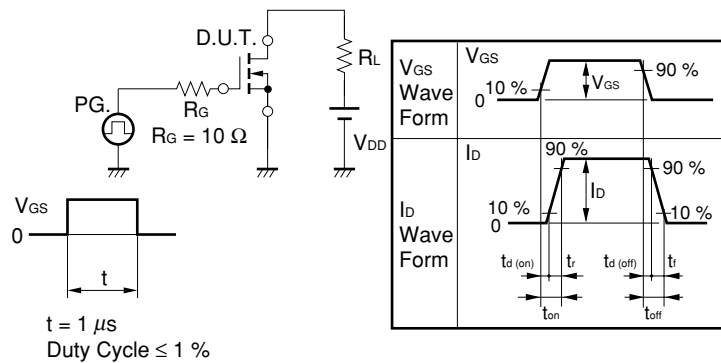
ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-Resistance	$R_{DS(on)1}$		52	70	mΩ	$V_{GS} = 10\text{ V}, I_D = 5.0\text{ A}$
Drain to Source On-Resistance	$R_{DS(on)2}$		68	95	mΩ	$V_{GS} = 4\text{ V}, I_D = 5.0\text{ A}$
Gate to Source Cutoff Voltage	$V_{GS(off)}$	1.0	1.6	2.0	V	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$
Forward Transfer Admittance	$ y_{fs} $	7.0	12		S	$V_{DS} = 10\text{ V}, I_D = 5.0\text{ A}$
Drain Leakage Current	I_{DSS}			10	μA	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$
Gate to Source Leakage Current	I_{GSS}			±10	μA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$
Input Capacitance	C_{iss}		860		pF	$V_{DS} = 10\text{ V}$
Output Capacitance	C_{oss}		440		pF	$V_{GS} = 0\text{ V}$
Reverse Transfer Capacitance	C_{rss}		110		pF	$f = 1\text{ MHz}$
Turn-On Delay Time	$t_{d(on)}$		15		ns	$I_D = 5.0\text{ A}$
Rise Time	t_r		90		ns	$V_{GS} = 10\text{ V}$
Turn-Off Delay Time	$t_{d(off)}$		75		ns	$V_{DD} = 30\text{ V}$
Fall Time	t_f		35		ns	$R_G = 10\ \Omega$
Total Gate Charge	Q_G		24		nC	$I_D = 10\text{ A}$
Gate to Source Charge	Q_{GS}		2.6		nC	$V_{DD} = 48\text{ V}$
Gate to Drain Charge	Q_{GD}		6.0		nC	$V_{GS} = 10\text{ V}$
Body Diode Forward Voltage	$V_{F(S-D)}$		1.0		V	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Time	t_{rr}		85		ns	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Charge	Q_{rr}		220		nC	$di/dt = 50\text{ A}/\mu\text{s}$

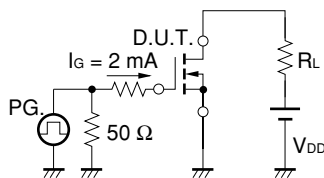
Test Circuit 1 Avalanche Capability



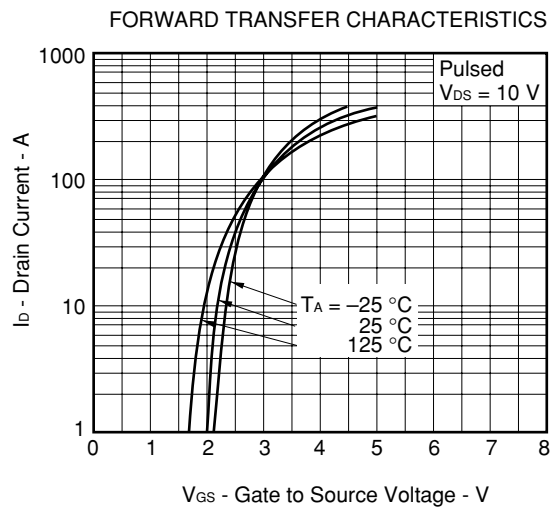
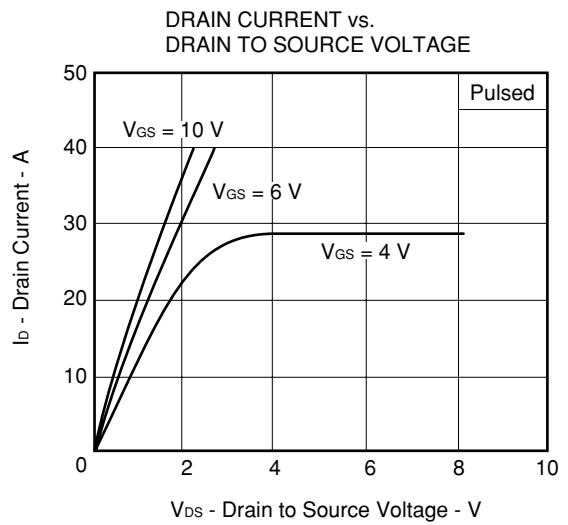
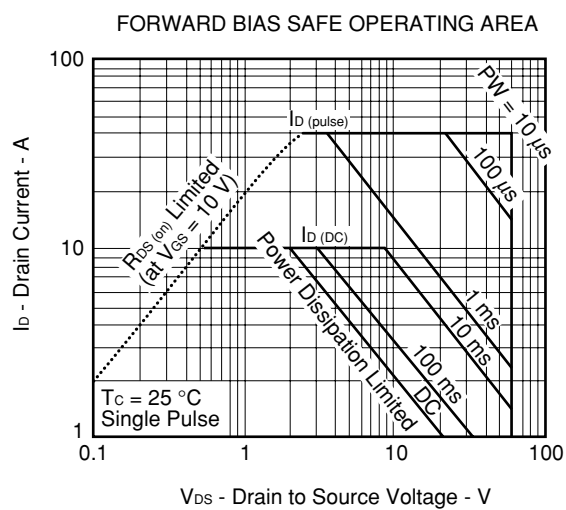
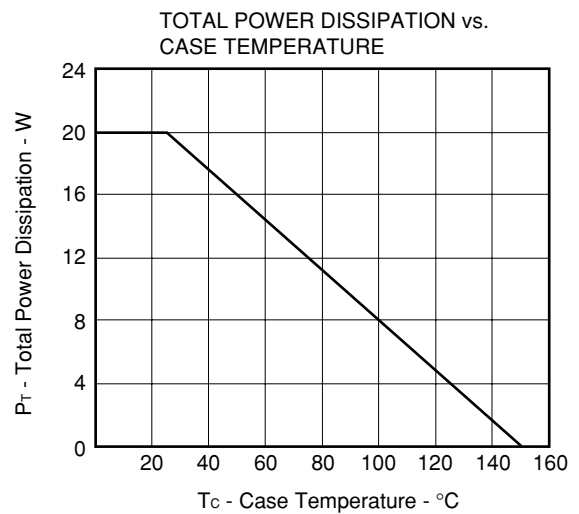
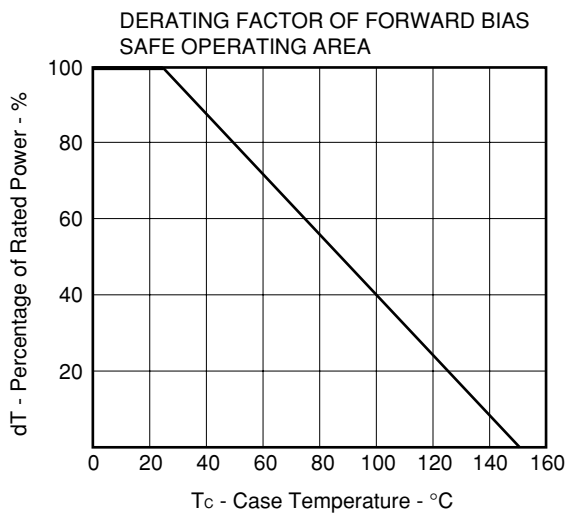
Test Circuit 2 Switching Time



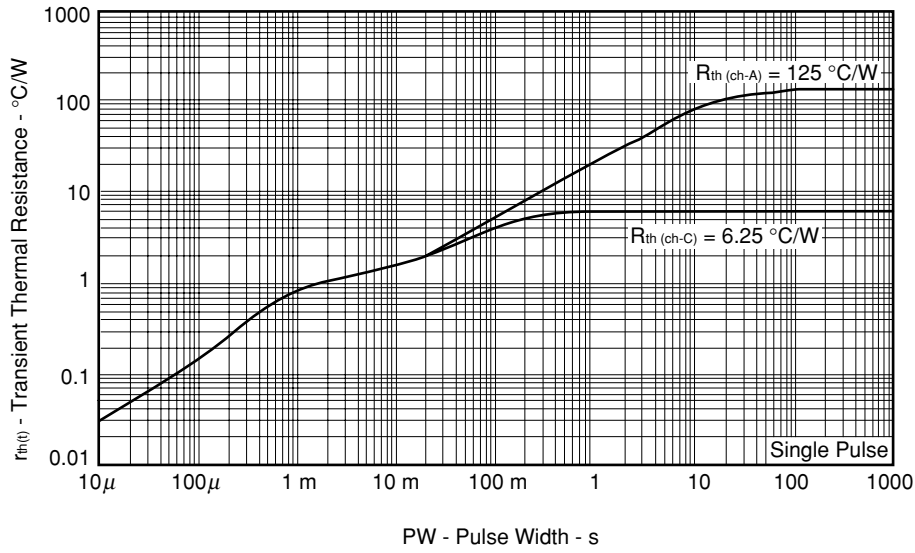
Test Circuit 3 Gate Charge



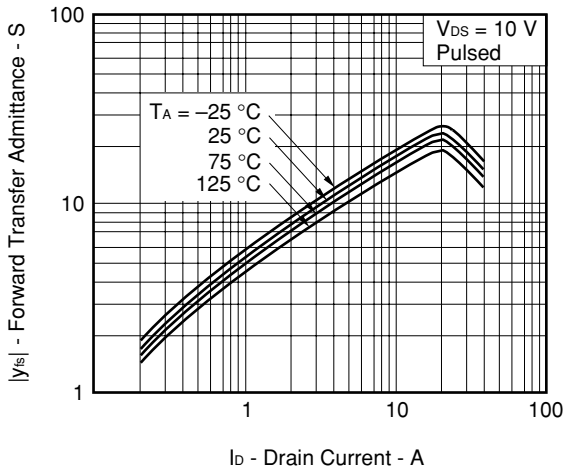
TYPICAL CHARACTERISTICS (T_A = 25 °C)



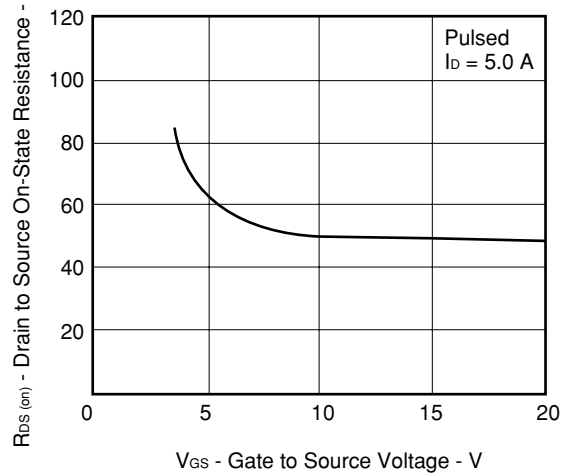
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



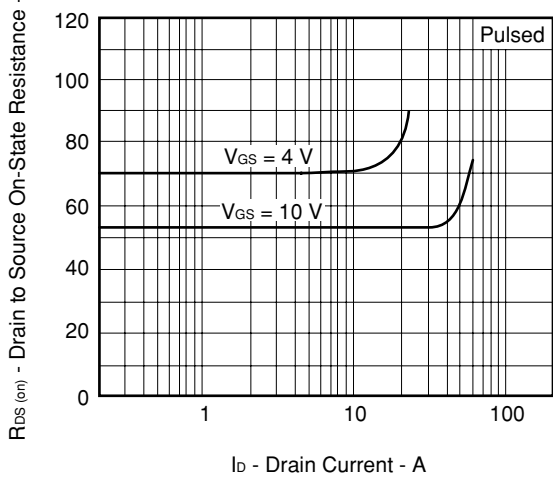
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



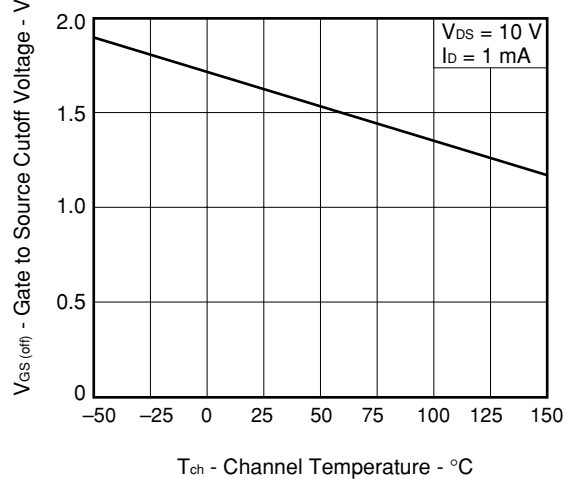
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

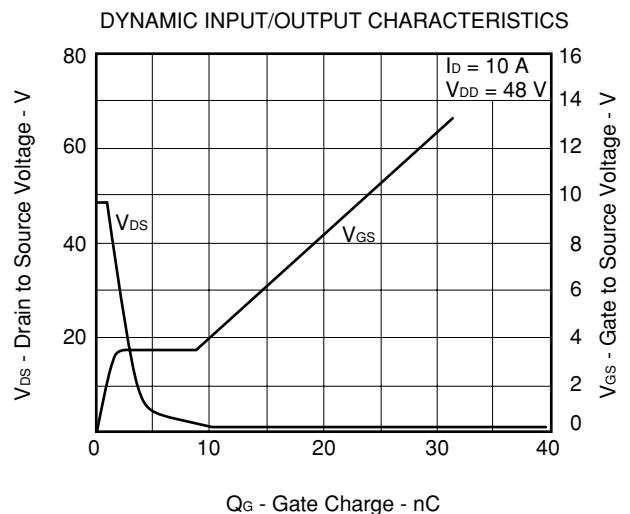
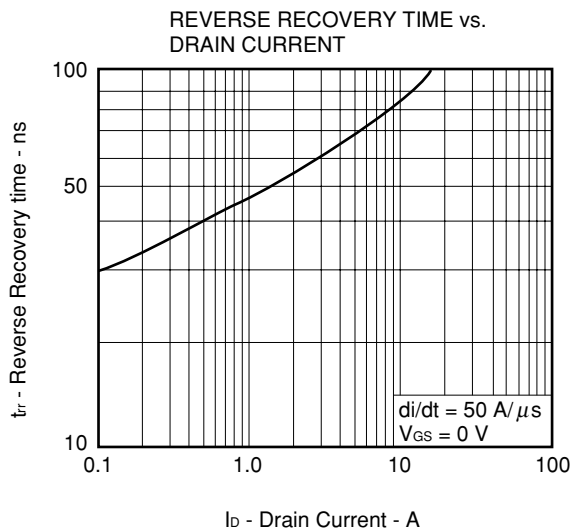
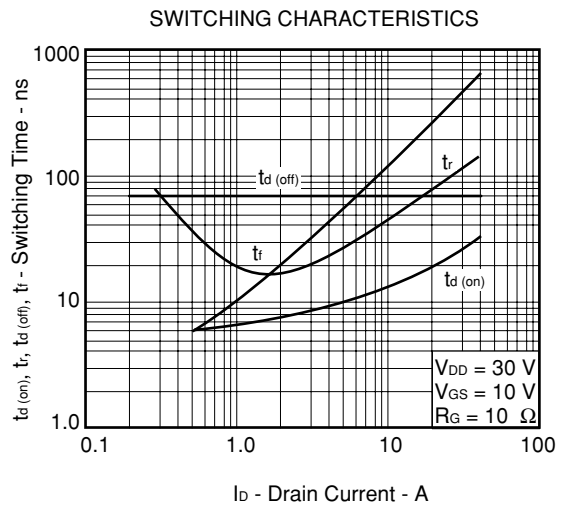
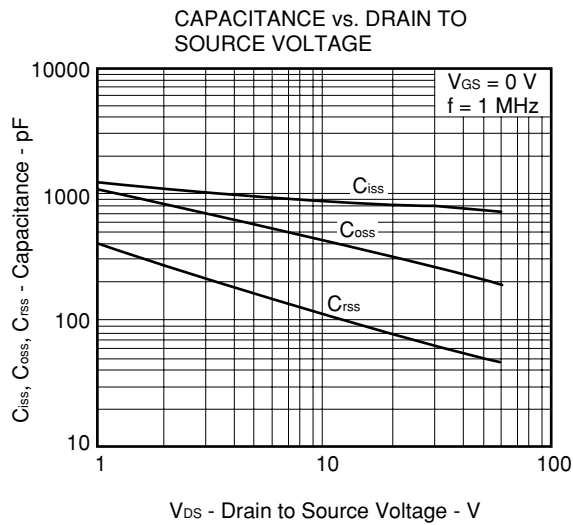
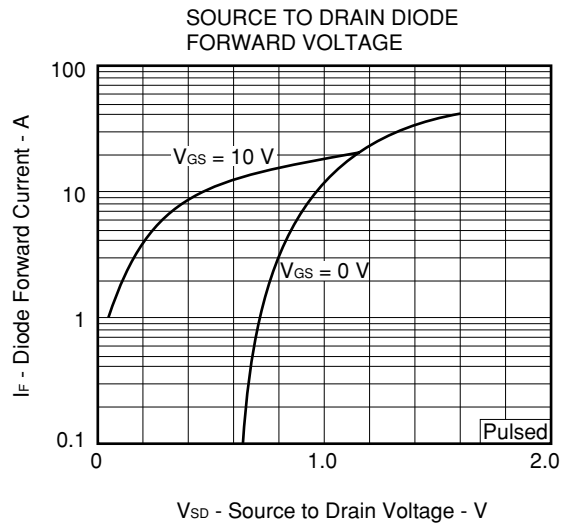
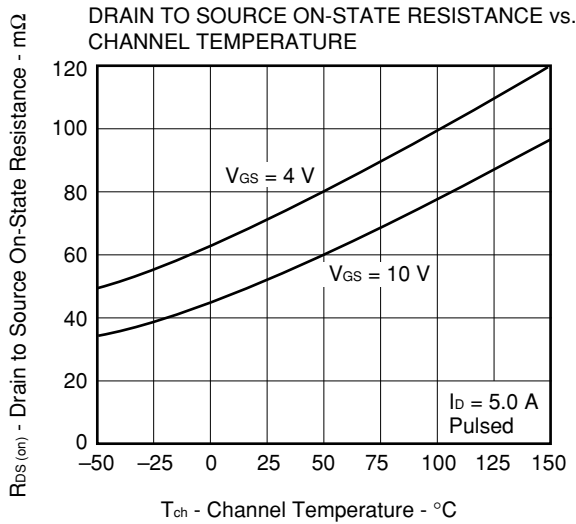


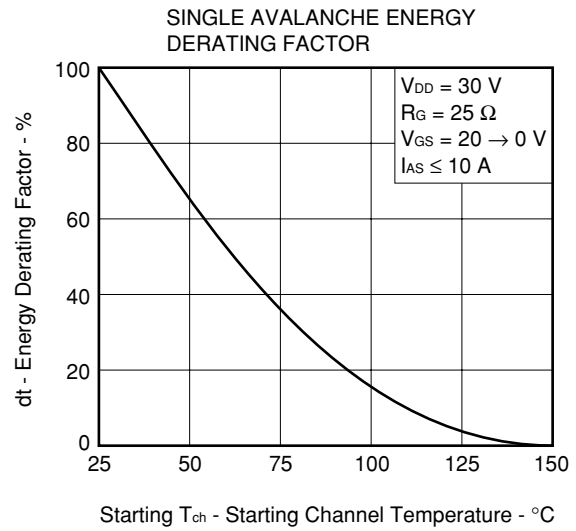
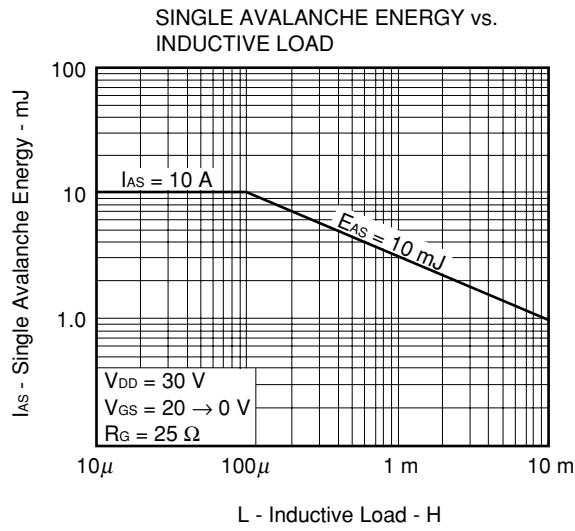
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE







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